

P-Channel Enhancement Mode Power MOSFET

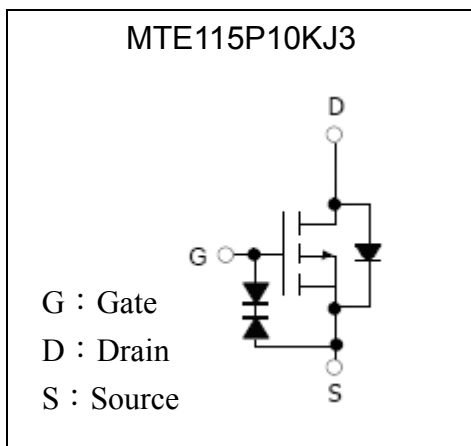
MTE115P10KJ3

| | |
|---|--------------------|
| BV_{DSS} | -100V |
| I_D@V_{GS}=-10V, T_C=25°C | -14A |
| R_{DS(ON)}@V_{GS}=-10V, I_D=-10A | 101mΩ (typ) |
| R_{DS(ON)}@V_{GS}=-6V, I_D=-10A | 120mΩ (typ) |

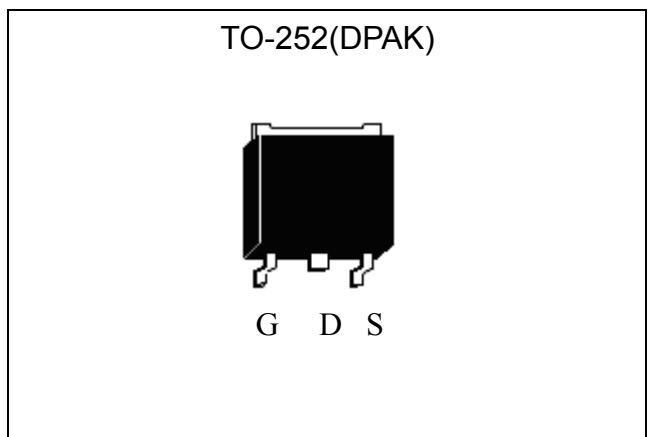
Features

- Low Gate Charge
- Simple Drive Requirement
- ESD Protected Gate
- Pb-free Lead Plating & Halogen-free Package

Equivalent Circuit

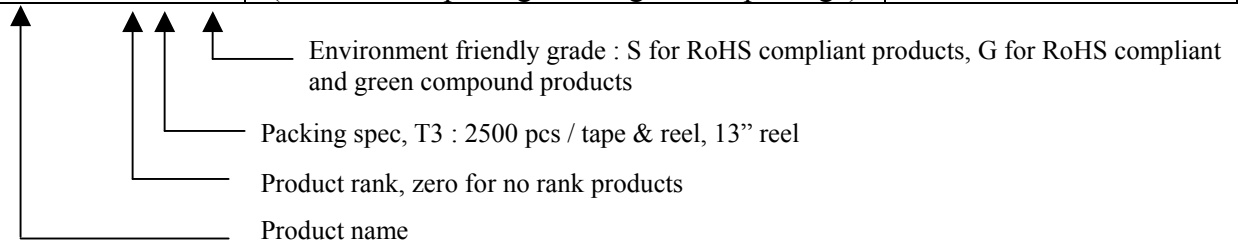


Outline



Ordering Information

| Device | Package | Shipping |
|---------------------|---|------------------------|
| MTE115P10KJ3-0-T3-G | TO-252 (Pb-free lead plating & halogen-free package) | 2500 pcs / Tape & Reel |



**Absolute Maximum Ratings** ($T_C=25^\circ\text{C}$, unless otherwise noted)

| Parameter | | Symbol | Limits | Unit |
|---|-------------------------------------|----------------|----------|------------------|
| Drain-Source Voltage | | V_{DS} | -100 | V |
| Gate-Source Voltage | | V_{GS} | ± 20 | |
| Continuous Drain Current @ $T_J=175^\circ\text{C}$, $T_C=25^\circ\text{C}$, $V_{GS}=-10\text{V}$ (Note 1) | | I_D | -14 | A |
| Continuous Drain Current @ $T_J=175^\circ\text{C}$, $T_C=100^\circ\text{C}$, $V_{GS}=-10\text{V}$ (Note 1) | | | -9.9 | |
| Continuous Drain Current @ $T_A=25^\circ\text{C}$, $V_{GS}=-10\text{V}$ (Note 2) | | I_{DSM} | -3.3 | |
| Continuous Drain Current @ $T_A=70^\circ\text{C}$, $V_{GS}=-10\text{V}$ (Note 2) | | | -2.6 | |
| Pulsed Drain Current (Note 3) | | I_{DM} | -56 | |
| Avalanche Current (Note 3) | | I_{AS} | -14 | |
| Avalanche Energy @ $L=0.7\text{mH}$, $I_D=-14\text{A}$, $R_G=25\Omega$ (Note 2) | | E_{AS} | 68 | mJ |
| Total Power Dissipation | $T_C=25^\circ\text{C}$ (Note 1) | P_D | 50 | W |
| | $T_C=100^\circ\text{C}$ (Note 1) | | 25 | |
| | $T_A=25^\circ\text{C}$ (Note 2) | P_{DSM} | 2.5 | |
| | $T_A=70^\circ\text{C}$ (Note 2) | | 1.6 | |
| Operating Junction and Storage Temperature Range | | T_J, T_{stg} | -55~+175 | $^\circ\text{C}$ |

Thermal Data

| Parameter | Symbol | Typical | Maximum | Unit |
|---|-----------------|---------|---------|---------------------------|
| Thermal Resistance, Junction-to-case | $R_{\theta JC}$ | 2.7 | 3 | $^\circ\text{C}/\text{W}$ |
| Thermal Resistance, Junction-to-ambient, $t \leq 10\text{s}$ (Note 2) | $R_{\theta JA}$ | 15 | 18 | |
| Thermal Resistance, Junction-to-ambient, steady state | | 40 | 50 | |

- Note : 1. The power dissipation P_D is based on $T_{J(\text{MAX})}=175^\circ\text{C}$, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.
2. The value of $R_{\theta JA}$ is measured with the device mounted on 1 in² FR-4 board with 2 oz. copper, in a still air environment with $T_A=25^\circ\text{C}$. The power dissipation P_{DSM} is based on $R_{\theta JA}$ and the maximum allowed junction temperature of 150°C . The value in any given application depends on the user's specific board design.
3. Pulse width limited by junction temperature $T_{J(\text{MAX})}=175^\circ\text{C}$. Ratings are based on low frequency and low duty cycles to keep initial $T_J=25^\circ\text{C}$.

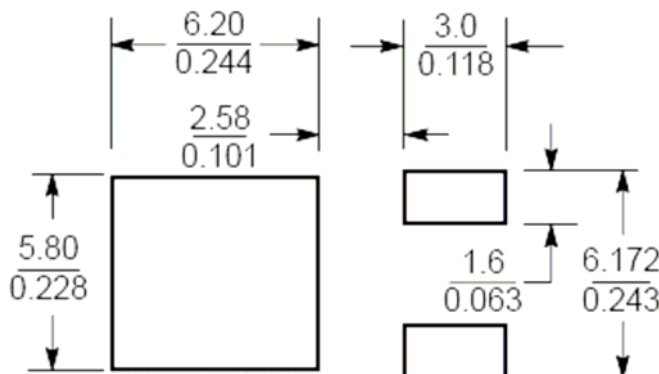


Characteristics (Tc=25°C, unless otherwise specified)

| Symbol | Min. | Typ. | Max. | Unit | Test Conditions |
|---|------|-------|------|------|--|
| Static | | | | | |
| BV _{DSS} | -100 | - | - | V | V _{GS} =0V, I _D =-250μA |
| V _{GS(th)} | -2 | - | -4 | | V _{DS} =V _{GS} , I _D =-250μA |
| I _{GSS} | - | - | ±10 | μA | V _{GS} =±20V, V _{DS} =0V |
| I _{DSS} | - | - | -1 | | V _{DS} =-80V, V _{GS} =0V |
| | - | - | -25 | | V _{DS} =-80V, V _{GS} =0V, T _J =125°C |
| I _{D(ON)} *1 | -14 | - | - | A | V _{DS} =-5V, V _{GS} =-10V |
| R _{DS(ON)} *1 | - | 101 | 135 | mΩ | V _{GS} =-10V, I _D =-10A |
| | - | 120 | 156 | | V _{GS} =-6V, I _D =-10A |
| G _{FS} *1 | - | 14 | - | S | V _{DS} =-5V, I _D =-10A |
| Dynamic | | | | | |
| Q _g *1, 2 | - | 18.6 | 27.9 | nC | I _D =-7A, V _{DS} =-80V, V _{GS} =-10V |
| Q _{gs} *1, 2 | - | 4.6 | - | | |
| Q _{gd} *1, 2 | - | 6.1 | - | | |
| t _{d(ON)} *1, 2 | - | 10.8 | 16.2 | ns | V _{DS} =-20V, I _D =-1A, V _{GS} =-10V, R _G =6Ω |
| t _r *1, 2 | - | 16.2 | 24.3 | | |
| t _{d(OFF)} *1, 2 | - | 72 | 108 | | |
| t _f *1, 2 | - | 64 | 96 | | |
| C _{iss} | - | 1002 | - | pF | V _{GS} =0V, V _{DS} =-25V, f=1MHz |
| C _{oss} | - | 117 | - | | |
| C _{rss} | - | 46 | - | | |
| R _g | - | 12 | - | Ω | V _{DS} =0V, f=1MHz |
| Source-Drain Diode Ratings and Characteristics | | | | | |
| I _S *1 | - | - | -14 | A | |
| I _{SM} *1 | - | - | -56 | | |
| V _{SD} *1 | - | -0.86 | -1.2 | V | I _S =-10A, V _{GS} =0V |
| t _{rr} | - | 27.9 | 41.8 | ns | I _F =-10A, dI _F /dt=100A/μs |
| Q _{rr} | - | 39 | - | nC | |

Note : *1.Pulse Test : Pulse Width ≤300μs, Duty Cycle≤2%
 *2.Independent of operating temperature
 *3.Pulse width limited by maximum junction temperature.

Recommended soldering footprint

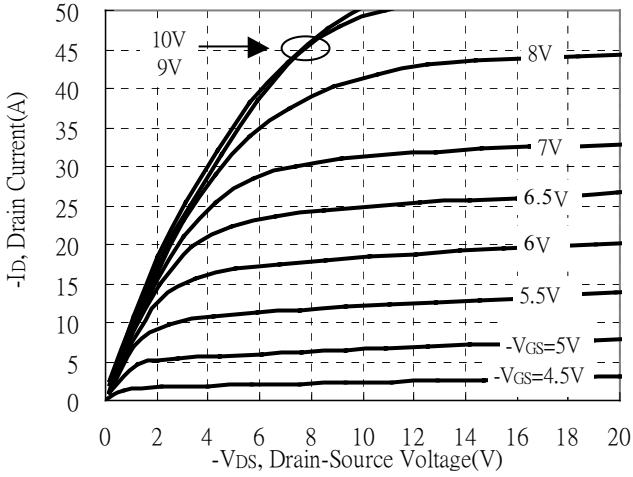


Unit ($\frac{\text{mm}}{\text{inch}}$)

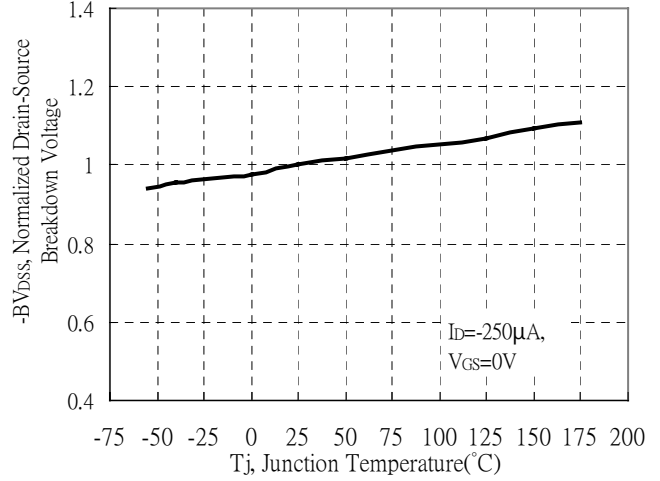


Typical Characteristics

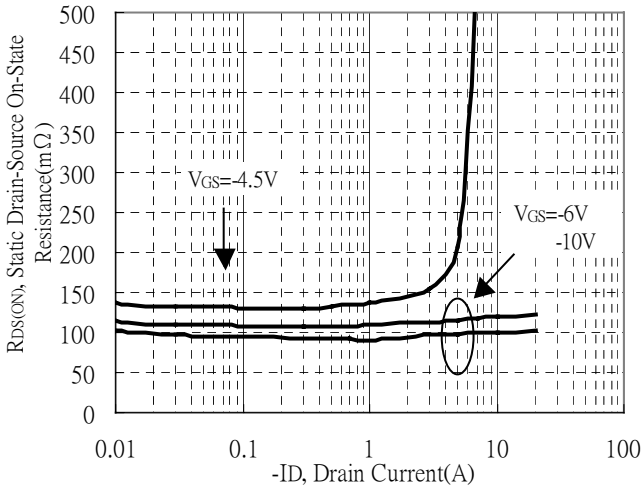
Typical Output Characteristics



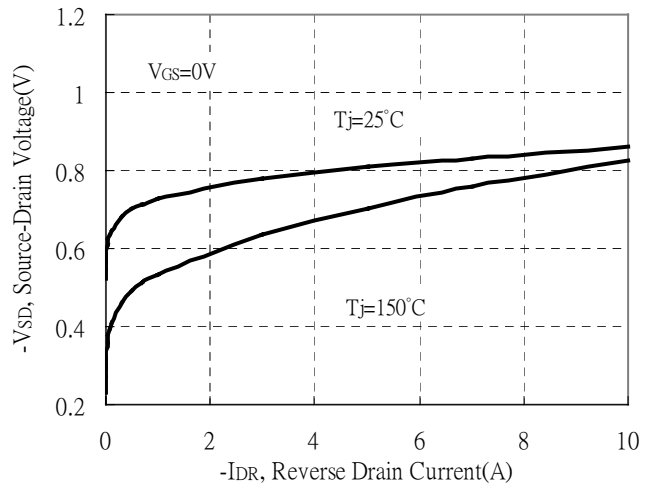
Brekdown Voltage vs Ambient Temperature



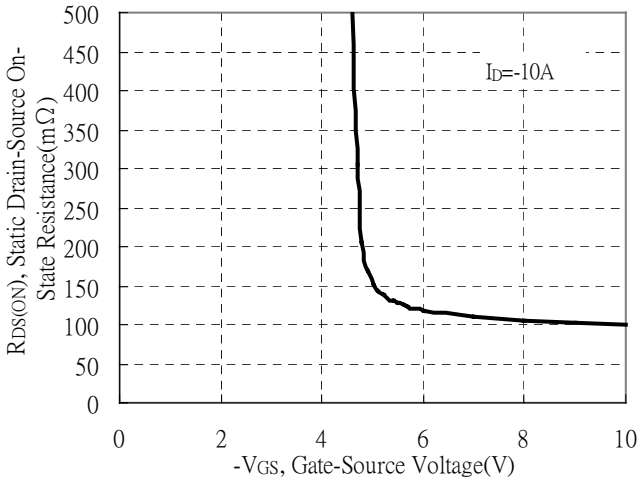
Static Drain-Source On-State resistance vs Drain Current



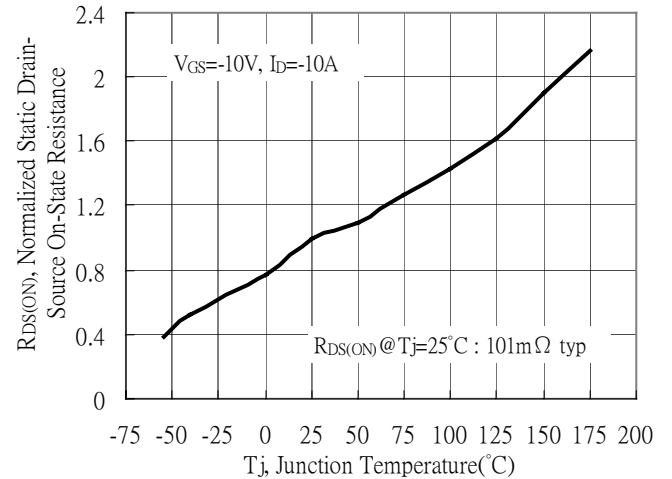
Reverse Drain Current vs Source-Drain Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage



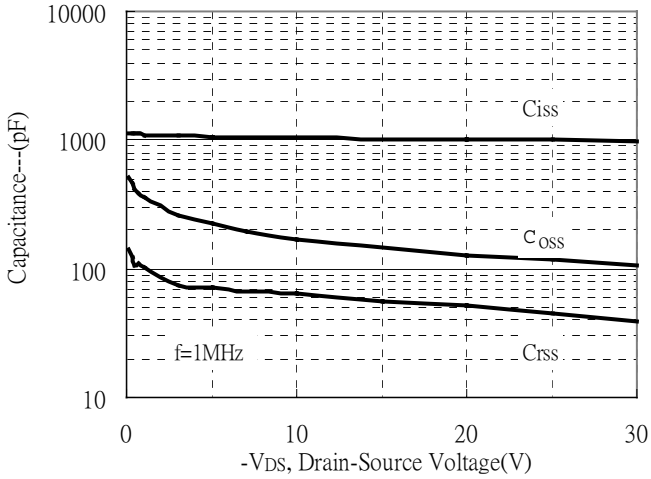
Drain-Source On-State Resistance vs Junction Temperature



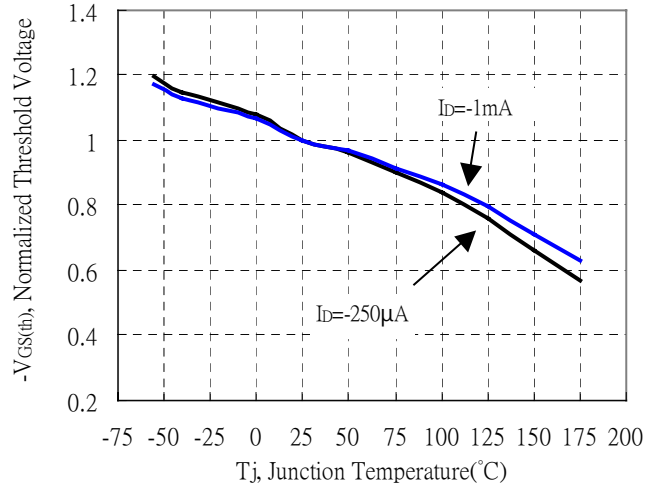


Typical Characteristics (Cont.)

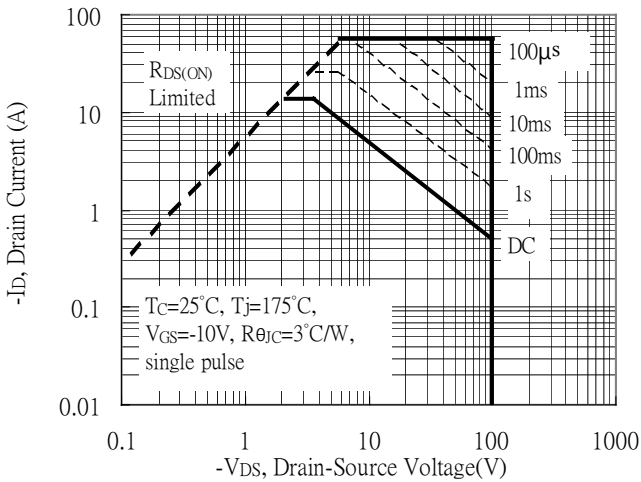
Capacitance vs Drain-to-Source Voltage



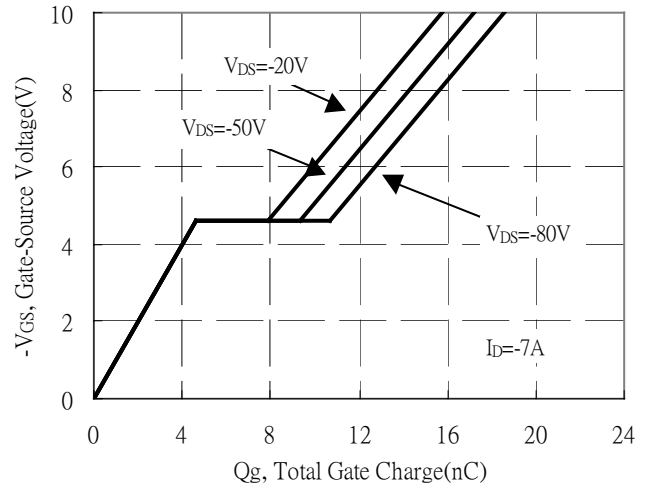
Threshold Voltage vs Junction Temperature



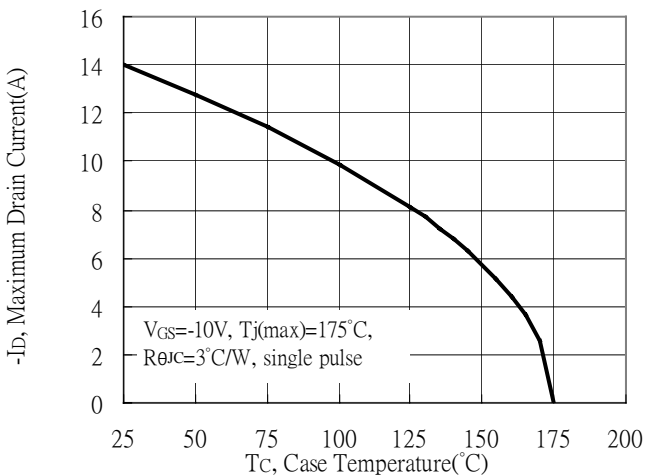
Maximum Safe Operating Area



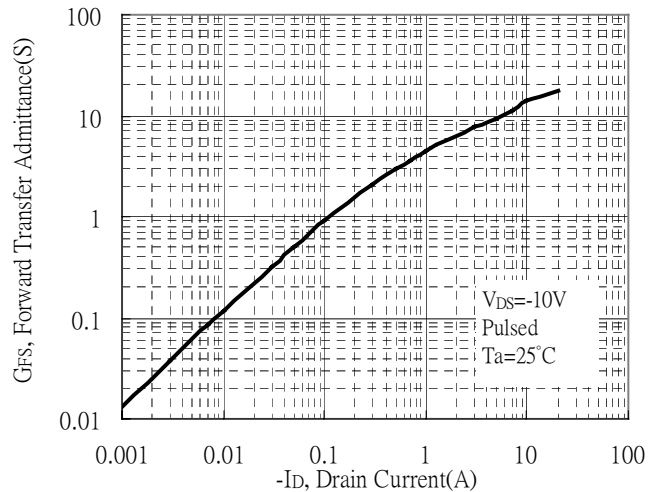
Gate Charge Characteristics



Maximum Drain Current vs Case Temperature



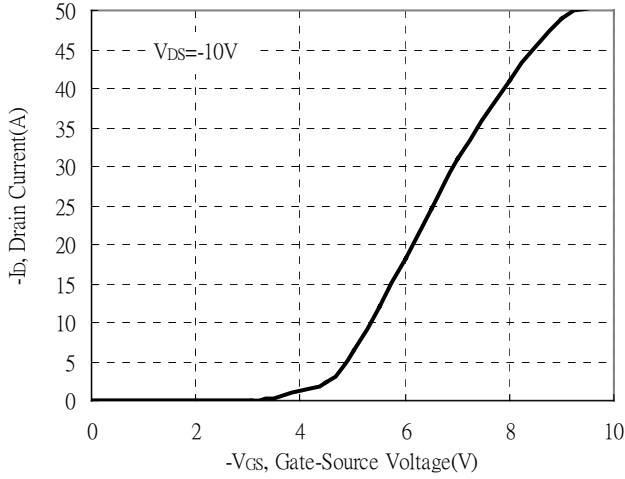
Forward Transfer Admittance vs Drain Current



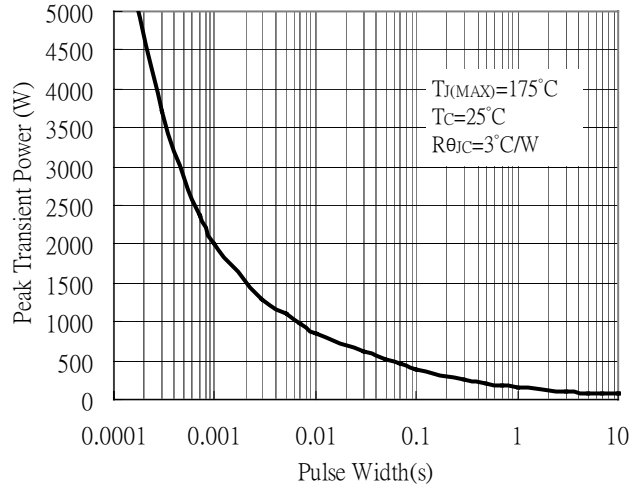


Typical Characteristics (Cont.)

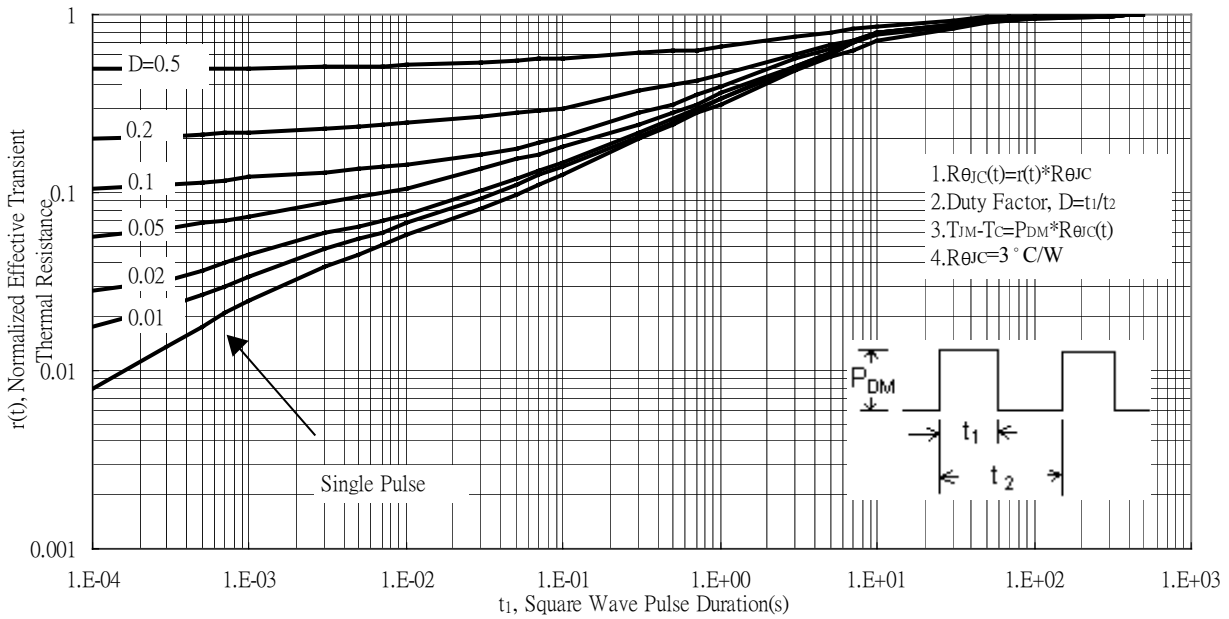
Typical Transfer Characteristics



Single Pulse Maximum Power Dissipation



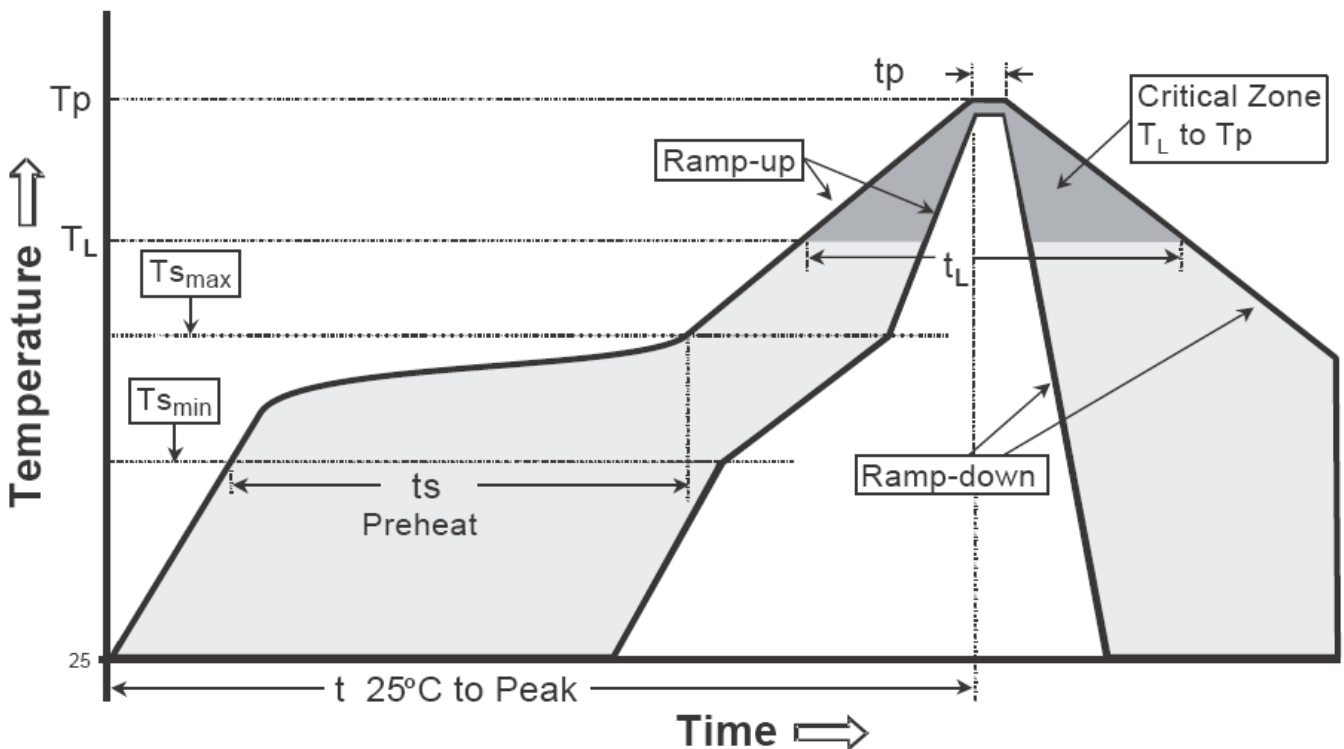
Transient Thermal Response Curves



Recommended wave soldering condition

| | | |
|-----------------|------------------|-----------------|
| Product | Peak Temperature | Soldering Time |
| Pb-free devices | 260 +0/-5 °C | 5 +1/-1 seconds |

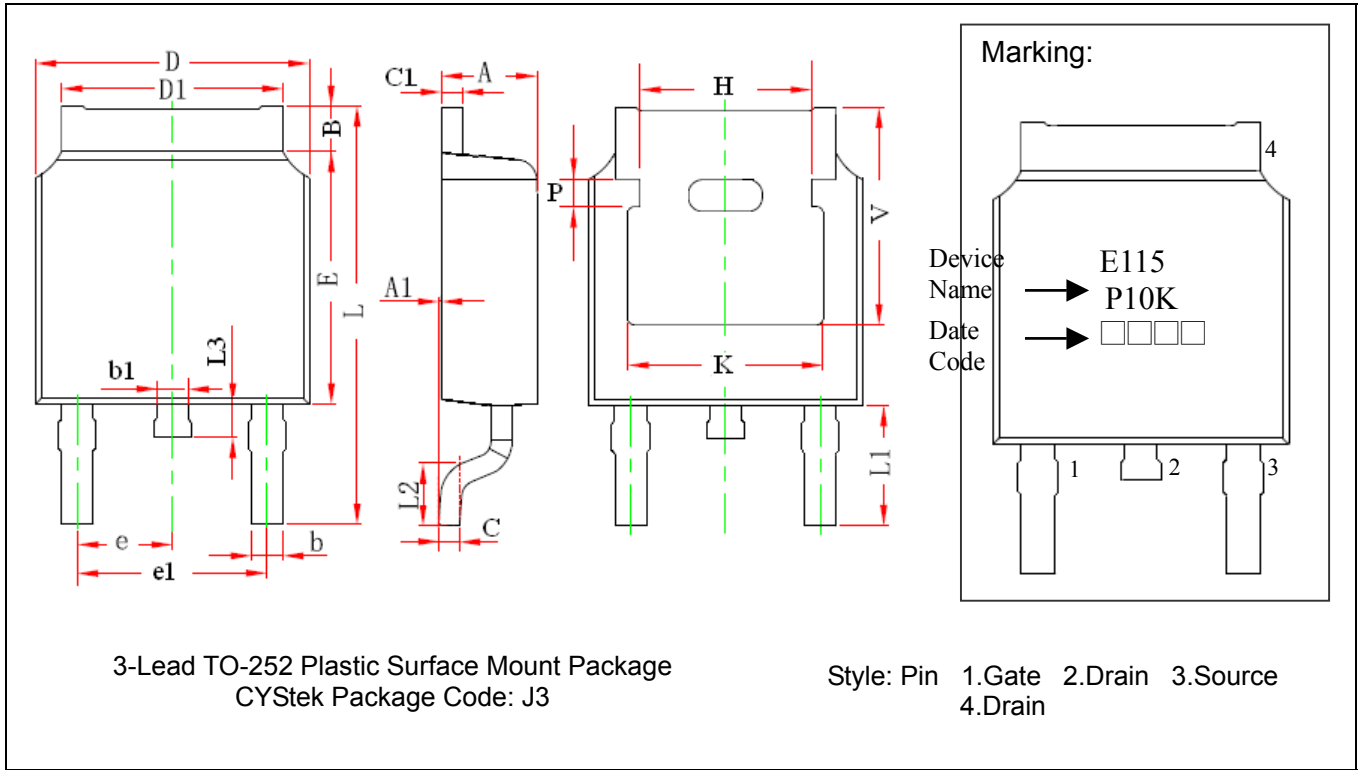
Recommended temperature profile for IR reflow



| Profile feature | Sn-Pb eutectic Assembly | Pb-free Assembly |
|---|-------------------------|------------------|
| Average ramp-up rate (Tsmax to Tp) | 3°C/second max. | 3°C/second max. |
| Preheat | | |
| -Temperature Min($T_{s \text{ min}}$) | 100°C | 150°C |
| -Temperature Max($T_{s \text{ max}}$) | 150°C | 200°C |
| -Time($t_{s \text{ min}}$ to $t_{s \text{ max}}$) | 60-120 seconds | 60-180 seconds |
| Time maintained above: | | |
| -Temperature (T_L) | 183°C | 217°C |
| - Time (t_L) | 60-150 seconds | 60-150 seconds |
| Peak Temperature(T_P) | 240 +0/-5 °C | 260 +0/-5 °C |
| Time within 5°C of actual peak temperature(t_p) | 10-30 seconds | 20-40 seconds |
| Ramp down rate | 6°C/second max. | 6°C/second max. |
| Time 25 °C to peak temperature | 6 minutes max. | 8 minutes max. |

Note : All temperatures refer to topside of the package, measured on the package body surface.

TO-252 Dimension



| DIM | Inches | | Millimeters | | DIM | Inches | | Millimeters | |
|-----|--------|-------|-------------|-------|-----|--------|-------|-------------|--------|
| | Min. | Max. | Min. | Max. | | Min. | Max. | Min. | Max. |
| A | 0.087 | 0.094 | 2.200 | 2.400 | e | 0.086 | 0.094 | 2.186 | 2.386 |
| A1 | 0.000 | 0.005 | 0.000 | 0.127 | e1 | 0.172 | 0.188 | 4.372 | 4.772 |
| B | 0.039 | 0.048 | 0.990 | 1.210 | H | 0.163 | REF | 4.140 | REF |
| b | 0.026 | 0.034 | 0.660 | 0.860 | K | 0.190 | REF | 4.830 | REF |
| b1 | 0.026 | 0.034 | 0.660 | 0.860 | L | 0.386 | 0.409 | 9.800 | 10.400 |
| C | 0.018 | 0.023 | 0.460 | 0.580 | L1 | 0.114 | REF | 2.900 | REF |
| C1 | 0.018 | 0.023 | 0.460 | 0.580 | L2 | 0.055 | 0.067 | 1.400 | 1.700 |
| D | 0.256 | 0.264 | 6.500 | 6.700 | L3 | 0.024 | 0.039 | 0.600 | 1.000 |
| D1 | 0.201 | 0.215 | 5.100 | 5.460 | P | 0.026 | REF | 0.650 | REF |
| E | 0.236 | 0.244 | 6.000 | 6.200 | V | 0.211 | REF | 5.350 | REF |

Notes: 1.Controlling dimension: millimeters.
 2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material:

- Lead : Pure tin plated.
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0.

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